

isc Silicon NPN Power Transistor

2SD1716

DESCRIPTION

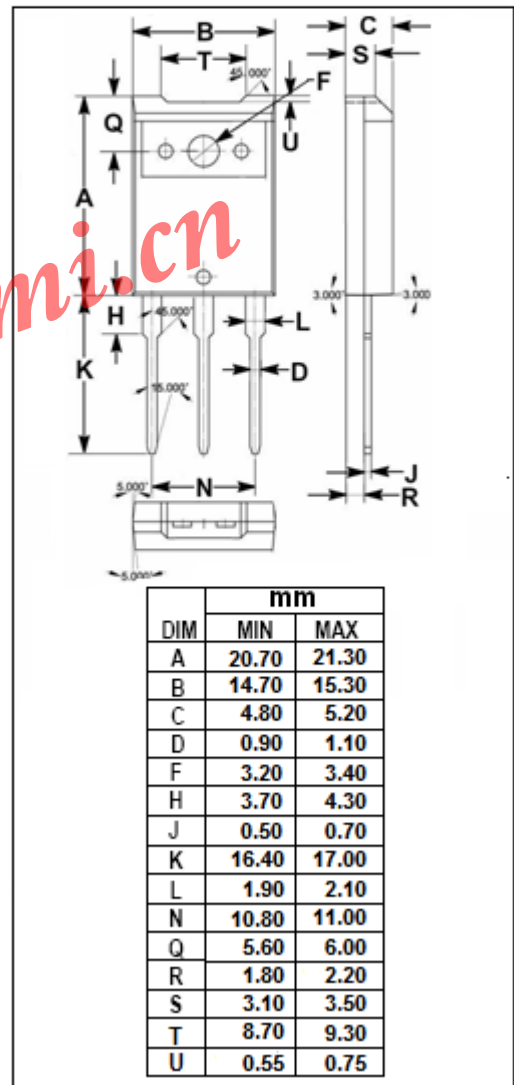
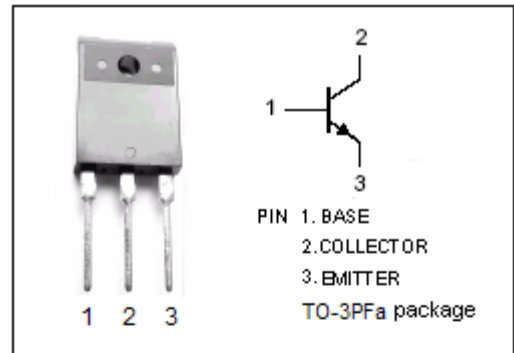
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 160V(\text{Min.})$
- Good Linearity of h_{FE}
- Wide Area of Safe Operation
- Complement to Type 2SB1161

APPLICATIONS

- Designed for high power amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	160	V
V_{CEO}	Collector-Emitter Voltage	160	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	12	A
I_{CP}	Collector Current-Pulse	20	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	120	W
	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	3	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=8A; I_B=0.8A$			2.0	V
$V_{BE(on)}$	Base -Emitter On Voltage	$I_C=8A; V_{CE}=5V$			1.8	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=160V; I_E=0$			50	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=3V; I_C=0$			50	μA
h_{FE-1}	DC Current Gain	$I_C=20mA; V_{CE}=5V$	20			
h_{FE-2}	DC Current Gain	$I_C=1A; V_{CE}=5V$	60		200	
h_{FE-3}	DC Current Gain	$I_C=8A; V_{CE}=5V$	20			
C_{OB}	Collector Output Capacitance	$I_E=0; V_{CB}=10V; f=1MHz$		250		pF
f_T	Current-Gain—Bandwidth Product	$I_C=0.5A; V_{CE}=5V$		20		MHz

◆ h_{FE-2} Classifications

Q	S	P
60-120	80-160	100-200